

Phototransistor, top view type

RPT-34PB3F

The RPT-34PB3F is a silicon planar phototransistor.

It is particularly suited for use with the ROHM SIR-34ST3F infrared light emitting diode.

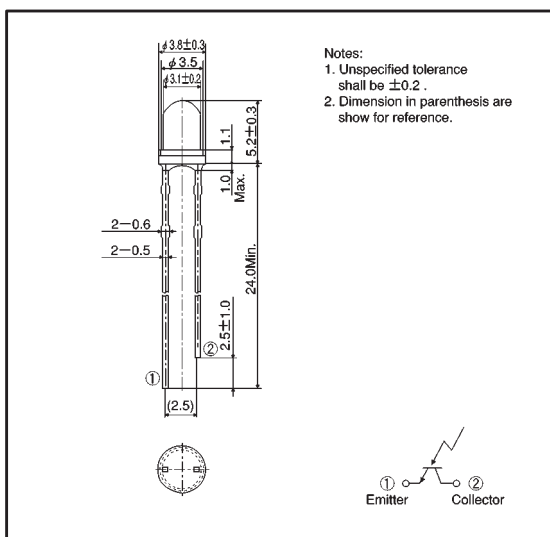
●Applications

Optical control equipment

●Features

- 1) High sensitivity.
- 2) Low cost plastic package.

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-emitter voltage	V_{CEO}	32	V
Emitter-collector voltage	V_{ECO}	5	V
Collector current	I_C	30	mA
Collector power dissipation	P_C	150	mW
Operating temperature	T_{opr}	-25~+85	°C
Storage temperature	T_{stg}	-30~+100	°C

●Electrical and optical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Light current	I_c	2.0	—	—	mA	$V_{CE}=5V, E=500Lx$
Dark current	I_{CEO}	—	—	0.5	μA	$V_{CE}=10V(\text{Black box})$
Peak sensitivity wavelength	λ_P	—	800	—	nm	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.4	V	$I_c=1mA, E=500Lx$
Half-angle	$\theta_{1/2}$	—	± 36	—	deg	—
Response time	$tr \cdot tf$	—	10	—	μs	$V_{CC}=5V, I_c=1mA, R_L=100\Omega$

●Electrical and optical characteristic curves

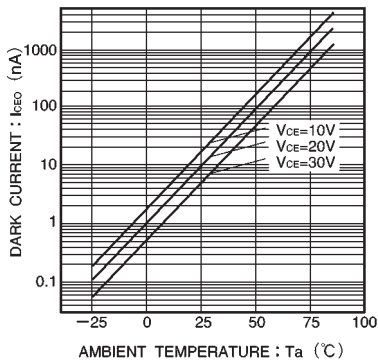


Fig.1 Dark current vs. ambient temperature

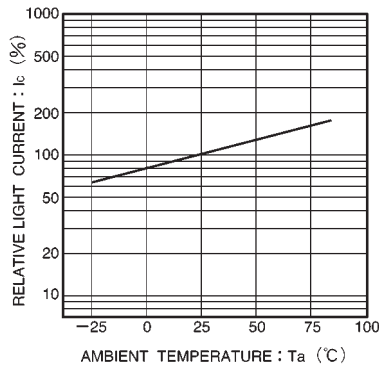


Fig.2 Relative output vs. ambient temperature

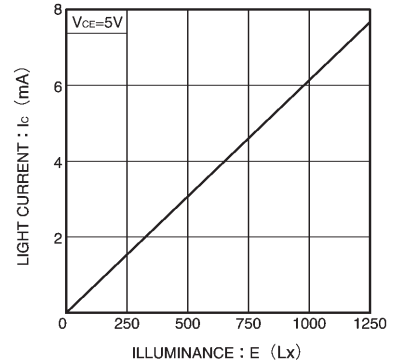


Fig.3 Light current vs. irradiance

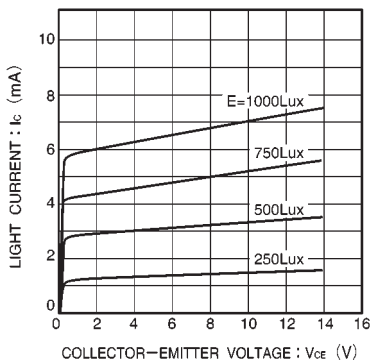


Fig.4 Output characteristics

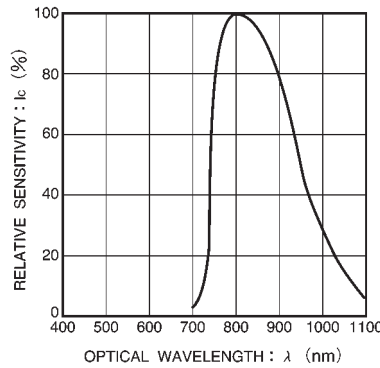


Fig.5 Spectral sensitivity

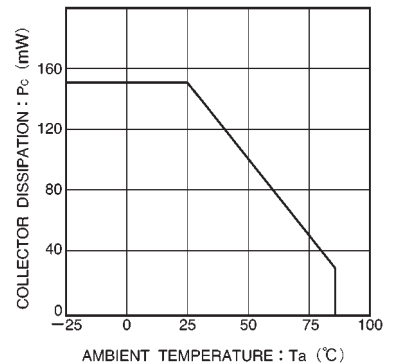


Fig.6 Collector dissipation vs. ambient temperature

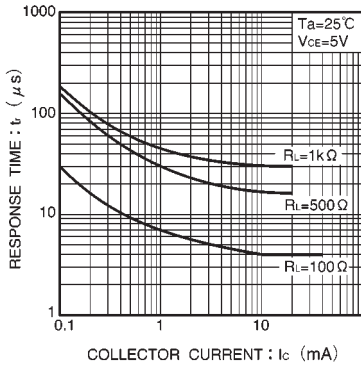


Fig.7 Response time vs. collector current

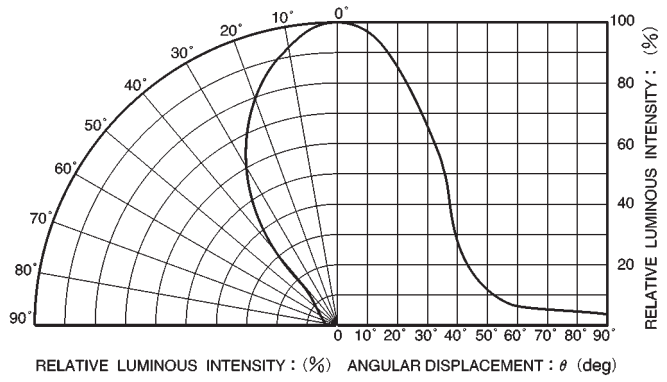


Fig.8 Directional pattern